



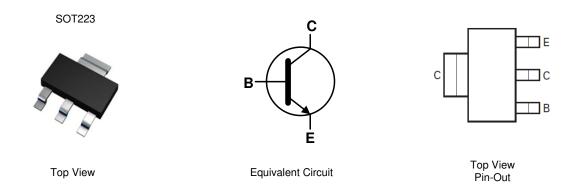
#### **30V NPN MEDIUM POWER HIGH CURRENT TRANSISTOR IN SOT223**

#### **Features**

- BV<sub>CEO</sub> > 30V
- I<sub>C</sub> = 7A High Continuous Collector Current
- I<sub>CM</sub> = 20A Peak Pulse Current
- P<sub>D</sub> = 3W Power Dissipation
- Extremely Low Equivalent On-Resistance; R<sub>CE(SAT)</sub> = 36Ω at 5A
- Very Low Saturation Voltages
- Complimentary PNP Type FZT949
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)



### Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FZT849TA	AEC-Q101	FZT849	7	12	1,000

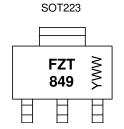
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



FZT 849 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 6 = 2016) WW or  $\overline{WW}$  = Week Code (01 to 53)



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	lc	7	A
Peak Pulse Current	I <sub>CM</sub>	20	A

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D	3 24	W	
Linear Derating Factor	(Note 6)	P <sub>D</sub> -	1.6 12.8	mW/°C	
Thermal Desistance, lunction to Archient	(Note 5)	$R_{ ext{ heta}JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ extsf{ heta}JA}$	78	°C/W	
Thermal Resistance, Junction to Lead	(Note 7)	R <sub>θJL</sub>	8.8		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in steady-state.

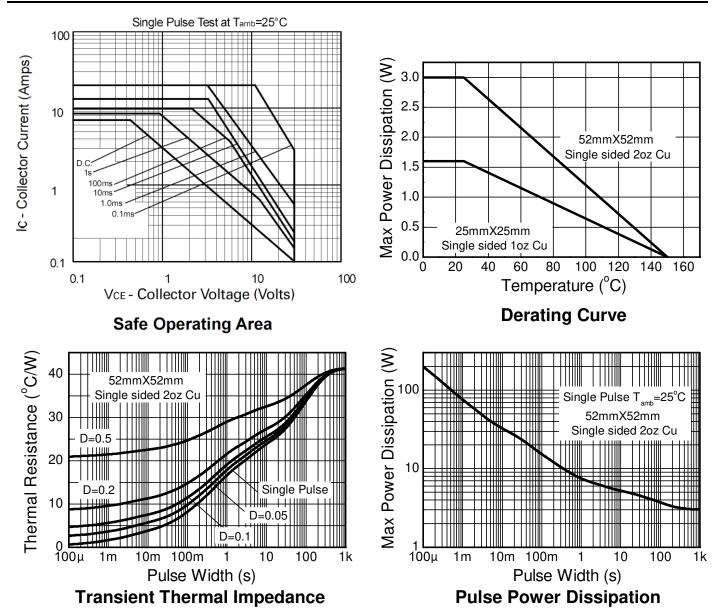
6. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.

Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



**FZT849** 

# **Thermal Characteristics and Derating Information**





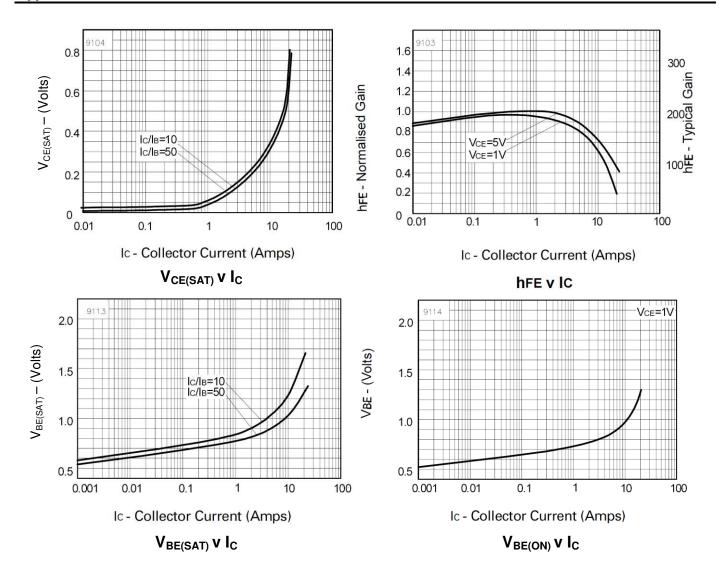
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	80	120		V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	80	120		V	$I_C = 1\mu A, R \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	30	40	_	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	8	_	V	I <sub>E</sub> = 100μA
Collector-Base Cut-Off Current	Ісво	_	_	50 1	nA μA	V <sub>CB</sub> = 70V V <sub>CB</sub> = 70V, T <sub>A</sub> = +100°C
		_	_	50	nA	$V_{CE}$ = 70V, $R \le 1k\Omega$
Collector Cut-Off Current	I <sub>CER</sub>		_	1	μA	$\label{eq:Vce} \begin{split} V_{CE} &= 70V, \ R \leq 1k\Omega, \ T_A = \\ +100^\circ C \end{split}$
Emitter Cut-Off Current	I <sub>EBO</sub>	_	_	10	nA	V <sub>EB</sub> = 6V
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(SAT)</sub>	_	35 67 188 —	50 110 215 350	mV	$\begin{split} I_{C} &= 500 \text{mA}, \ I_{B} = 20 \text{mA} \\ I_{C} &= 1\text{A}, \ I_{B} = 20 \text{mA} \\ I_{C} &= 2\text{A}, \ I_{B} = 20 \text{mA} \\ I_{C} &= 6.5\text{A}, \ I_{B} = 300 \text{mA} \end{split}$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(SAT)</sub>	_	_	1.2	V	$I_{C} = 6.5A, I_{B} = 300mA$
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(ON)</sub>		_	1.13	V	$I_{C} = 6.5A, V_{CE} = 1V$
DC Current Gain (Note 9)	h <sub>FE</sub>	100 100 100 30	200 200 150 65	 300 		$      I_{C} = 10 mA, V_{CE} = 1V \\       I_{C} = 1A, V_{CE} = 1V \\       I_{C} = 7A, V_{CE} = 1V \\       I_{C} = 20A, V_{CE} = 2V $
Transitional Frequency	fT	100	_	_	MHz	$I_{C} = 100 \text{mA}, V_{CE} = 10 \text{V}$ f = 50MHz
Output Capacitance	C <sub>OBO</sub>		75		pF	V <sub>CB</sub> = 10V, f = 1MHz
Switching Time	t <sub>ON</sub> t <sub>OFF</sub>		45 630		ns ns	$I_{C} = 1A, I_{B1} = 100mA$ $I_{B2} = -100mA, V_{CC} = 10V$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



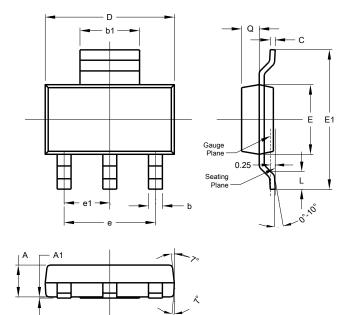


**FZT849** 

# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

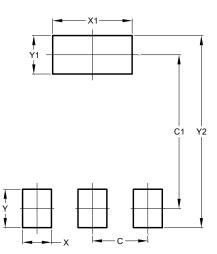
SOT223



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
ш	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All D	All Dimensions in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

FZT849 Document number: DS33173 Rev. 5 - 2 SOT223



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